

LISTING OF THE CLAIMS

1 (original): A seed crystal consisting of a silicon carbide single crystal, comprising:

a single crystal growing face inclined at an angle ranging from 3 degrees or more to 60 degrees or less with respect to the (11-20) face to a direction inclined at an angle ranging from -45 degrees or more to 45 degrees or less from a <0001> direction to the [1-100] direction.

2 (original): The seed crystal according to claim 1, wherein said <0001> direction is the [0001] Si direction.

3 (original): The seed crystal according to claim 1, wherein said single crystal growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

4 (original): The seed crystal according to claim 2, wherein said single crystal growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

5 (original): The seed crystal according to claim 1, wherein said single crystal growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

6 (original): The seed crystal according to claim 2, wherein said single crystal growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

7 (original): The seed crystal according to claim 1, wherein said <0001> direction is the [000-1] C direction.

8 (original): The seed crystal according to claim 7, wherein said single crystal growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

9 (original): The seed crystal according to claim 7, wherein said single crystal growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

10 (original): A single crystal substrate consisting of a silicon carbide single crystal, comprising:

an epitaxial growing face inclined at an angle ranging from 3 degrees or more to 60 degrees or less with respect to the (11-20) face to a direction inclined at an angle ranging from -45 degrees or more to 45 degrees or less from a <0001> direction to the [1-100] direction.

11 (original): The single crystal substrate according to claim 10, wherein said <0001> direction is the [0001] Si direction.

12 (original): The single crystal substrate according to claim 10, wherein said epitaxial growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

13 (original): The single crystal substrate according to claim 11, wherein said epitaxial growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

14 (original): The single crystal substrate according to claim 10, wherein said epitaxial growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

15 (original): The single crystal substrate according to claim 11, wherein said epitaxial growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

16 (original): The single crystal substrate according to claim 10, wherein said <0001> direction is the [000-1] C direction.

17 (original): The single crystal substrate according to claim 16, wherein said epitaxial growing face is inclined at an angle ranging from 3 degrees or more to 30 degrees or less with respect to said (11-20) face.

18 (original): The single crystal substrate according to claim 16, wherein said epitaxial growing face is inclined at an angle ranging from 6 degrees or more to 30 degrees or less with respect to said (11-20) face.

Claims 19 to 36 (canceled).